

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

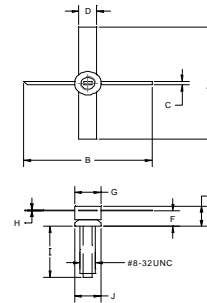
The **ASI MLN2027SS** is Designed for

**FEATURES:**

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- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	10 A
<b>V<sub>CB</sub></b>	60 V
<b>V<sub>CE</sub></b>	35 V
<b>P<sub>DISS</sub></b>	140 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +150 °C
<b>θ<sub>JC</sub></b>	25 °C/W

**PACKAGE STYLE .205 4L STUD**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.976 / 24.800	1.000 / 25.4000
B	.976 / 24.800	1.000 / 25.4000
C	.028 / 0.700	.031 / 0.800
D	.138 / 3.500	
E	.161 / 4.100	.196 / 5.000
F	.098 / 2.500	.110 / 2.800
G	.200 / 5.100	.208 / 5.300
H	.004 / 0.100	.006 / 0.150
I	.425 / 10.800	.465 / 11.800
J	.200 / 5.100	2.05 / 5.200

**ORDER CODE: ASI10631**
**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 50 mA	35			<b>V</b>
<b>BV<sub>CER</sub></b>	I <sub>C</sub> = 50 mA      R <sub>BE</sub> = 10 Ω	60			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 10 mA	4.0			<b>V</b>
<b>I<sub>CES</sub></b>	V <sub>E</sub> = 28 V			5	<b>mA</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V      I <sub>C</sub> = 1.0 A	10		100	<b>---</b>
<b>C<sub>ob</sub></b>	V <sub>CB</sub> = 28 V      f = 1.0 MHz			4.0	<b>pF</b>
<b>P<sub>GE</sub></b>	V <sub>CE</sub> = 25 V      I <sub>CQ</sub> = 100 mA      f = 2.0 GHz P <sub>OUT</sub> = 0.5 W	6.0			<b>dB</b>